

# RD74LVC125B

## Quad. Bus Buffer Gates with 3-state Outputs

REJ03D0498-0200 Rev.2.00 Dec. 10, 2004

#### **Description**

The RD74LVC125B has four bus buffer gates in a 14 pin package. The device requires the three state control input  $\overline{\text{OE}}$  to be taken high to put the output into the high impedance condition. Low voltage and high-speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

#### **Features**

•  $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$ 

• All inputs  $V_{IH}$  (Max.) = 5.5 V (@ $V_{CC}$  = 0 V to 5.5 V)

• All outputs  $V_{OUT}$  (Max.) = 5.5 V (@ $V_{CC}$  = 0 V or output off state)

• Typical  $V_{OL}$  ground bounce < 0.8 V (@ $V_{CC}$  = 3.3 V, Ta = 25°C)

• Typical  $V_{OH}$  undershoot > 2.0 V (@ $V_{CC}$  = 3.3 V, Ta = 25°C)

• High output current  $\pm 4 \text{ mA} (@V_{CC} = 1.65 \text{ V})$ 

 $\pm 8 \text{ mA } (@V_{CC} = 2.3 \text{ V})$ 

 $\pm 12 \text{ mA } (@V_{CC} = 2.7 \text{ V})$ 

 $\pm 24 \text{ mA } (@V_{CC} = 3.0 \text{ V to } 5.5 \text{ V})$ 

• Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
RD74LVC125BFPEL	SOP-14 pin (JEITA)	FP-14DAV	FP	EL (2,000 pcs/reel)
RD74LVC125BTELL	TSSOP-14 pin	TTP-14DV	Т	ELL (2,000 pcs/reel)

#### **Function Table**

Inp		
ŌĒ	Α	Outputs Y
Н	X	Z
L	L	L
L	Н	Н

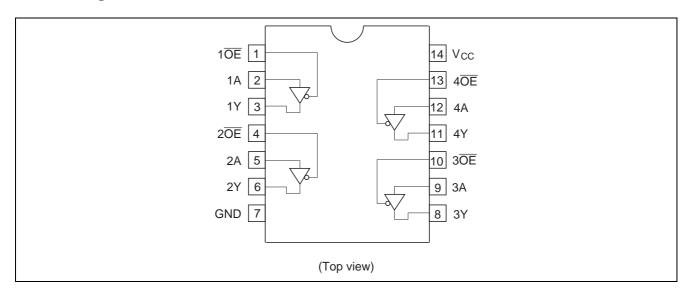
H: High level

L: Low level

X: Immaterial

Z: High impedance

## **Pin Arrangement**



## **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V <sub>CC</sub>	–0.5 to 7.0	V	
Input diode current	I <sub>IK</sub>	<b>–</b> 50	mA	$V_1 = -0.5 \text{ V}$
Input voltage	VI	–0.5 to 7.0	V	
Output diode current	I <sub>OK</sub>	-50	mA	$V_0 = -0.5 \text{ V}$
		50		$V_O = V_{CC} + 0.5 \text{ V}$
Output voltage	Vo	–0.5 to V <sub>CC</sub> +0.5	V	Output "H" or "L"
		–0.5 to 7.0		Output "Z" or V <sub>CC</sub> : OFF
Output current	Io	±50	mA	
V <sub>CC</sub> , GND current / pin	I <sub>CC</sub> or I <sub>GND</sub>	±100	mA	
Storage temperature	Tstg	–65 to +150	°C	

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

## **Recommended Operating Conditions**

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V <sub>CC</sub>	1.5 to 5.5	V	Data hold
		1.65 to 5.5		At operation
Input / output voltage	Vı	0 to 5.5	V	
	Vo	0 to V <sub>CC</sub>	V	Output "H" or "L"
		0 to 5.5		Output "Z" or V <sub>CC</sub> : OFF
Operating temperature	Та	-40 to 85	°C	
Output current	I <sub>ОН</sub>	-4	mA	V <sub>CC</sub> = 1.65 V
		-8		V <sub>CC</sub> = 2.3 V
		-12		V <sub>CC</sub> = 2.7 V
		-24		V <sub>CC</sub> = 3.0 V to 5.5 V
	I <sub>OL</sub>	4	mA	V <sub>CC</sub> = 1.65 V
		8		V <sub>CC</sub> = 2.3 V
		12		V <sub>CC</sub> = 2.7 V
		24		V <sub>CC</sub> = 3.0 V to 5.5 V
Input rise / fall time *1	t <sub>r</sub> , t <sub>f</sub>	20	ns/V	V <sub>CC</sub> = 1.65 V to 2.7 V
		10		V <sub>CC</sub> = 3.0 V to 5.5 V

Note: 1. This item guarantees maximum limit when one input switches.

Waveform: Refer to test circuit of switching characteristics.

### **Electrical Characteristics**

			Ta = -40 to 85°C			
Item	Symbol	V <sub>CC</sub> (V)	Min	Max	Unit	Test Conditions
Input voltage	V <sub>IH</sub>	1.65 to 1.95	V <sub>CC</sub> ×0.65	_	V	
		2.3 to 2.7	1.7	_		
		2.7 to 3.6	2.0	_		
		4.5 to 5.5	V <sub>CC</sub> ×0.7	_		
	V <sub>IL</sub>	1.65 to 1.95	_	V <sub>CC</sub> ×0.35	V	
		2.3 to 2.7	_	0.7		
		2.7 to 3.6	_	0.8		
		4.5 to 5.5	_	V <sub>CC</sub> ×0.3		
Output voltage	V <sub>OH</sub>	1.65 to 5.5	V <sub>CC</sub> -0.2	_	V	$I_{OH} = -100 \mu A$
		1.65	1.2	_		$I_{OH} = -4 \text{ mA}$
		2.3	1.7	_		$I_{OH} = -8 \text{ mA}$
		2.7	2.2	_		$I_{OH} = -12 \text{ mA}$
		3.0	2.4	_		
		3.0	2.2	_		$I_{OH} = -24 \text{ mA}$
		4.5	3.8	_		
	$V_{OL}$	1.65 to 5.5	_	0.2	V	I <sub>OL</sub> = 100 μA
		1.65	_	0.45		I <sub>OL</sub> = 4 mA
		2.3	_	0.7		I <sub>OL</sub> = 8 mA
		2.7	_	0.4		I <sub>OL</sub> = 12 mA
		3.0	_	0.55		I <sub>OL</sub> = 24 mA
		4.5	_	0.55		
Input current	I <sub>IN</sub>	0 to 5.5	_	±5.0	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Output leak current	I <sub>OFF</sub>	0	_	±5.0	μΑ	V <sub>IN</sub> / V <sub>OUT</sub> = 5.5 V
Off state output current	l <sub>OZ</sub>	2.7 to 5.5		±5.0	μΑ	V <sub>IN</sub> = V <sub>CC</sub> or GND,
						V <sub>OUT</sub> = 5.5 V or GND
Quiescent supply current	I <sub>CC</sub>	2.7 to 3.6	_	±5.0	μΑ	V <sub>IN</sub> = 3.6 V to 5.5 V
		2.7 to 5.5	_	5.0		$V_{IN} = V_{CC}$ or GND
	$\Delta I_{CC}$	2.7 to 3.6		500	μΑ	$V_{IN}$ = one input at ( $V_{CC}$ –0.6) V, other inputs at $V_{CC}$ or GND



## **Switching Characteristics**

			Ta = -40 to 85°C				From	То
Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	(Input)	(Output)
Propagation delay time	t <sub>PLH</sub>	1.8±0.15	1.0	_	12.3	ns	Α	Υ
	t <sub>PHL</sub>	2.5±0.2	1.0	_	6.3			
		2.7	1.0	_	5.5			
		3.3±0.3	1.0	_	4.8			
		5.0±0.5	1.0	_	3.8			
Output enable time	t <sub>ZH</sub>	1.8±0.15	1.0	_	14.3	ns	ŌE	Υ
	$t_{ZL}$	2.5±0.2	1.0	_	7.4			
		2.7	1.0	_	6.6			
		3.3±0.3	1.0	_	5.4			
		5.0±0.5	1.0	_	4.4			
Output disable time	t <sub>HZ</sub>	1.8±0.15	1.0	_	11.1	ns	ŌĒ	Υ
	$t_{LZ}$	2.5±0.2	1.0	_	5.6			
		2.7	1.0	_	5.0			
		3.3±0.3	1.0	_	4.6			
		5.0±0.5	1.0	_	3.6			
Between output pins skew *	t <sub>OSLH</sub>	1.8±0.15	_	_	_	ns		
	t <sub>OSHL</sub>	2.5±0.2	_	_	_			
		2.7	_	_	_			
		3.3±0.3	_	_	1.0			
		5.0±0.5	_	_	1.0			
Input capacitance	C <sub>IN</sub>	3.3	_	4.0	_	pF		
Output capacitance	Co	3.3	_	7.0	_	pF		

Note: 1. This parameter is characterized but not tested.

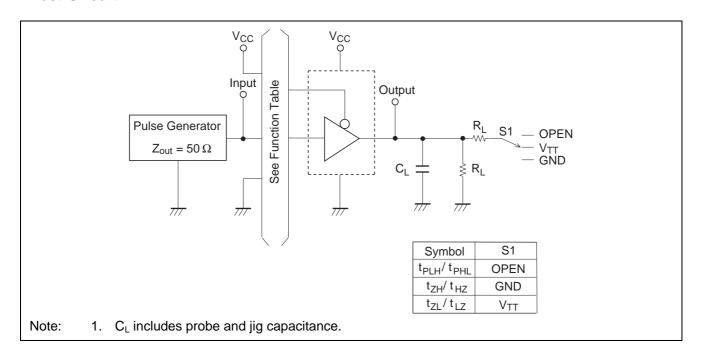
 $tos_{LH} = |\ t_{PLHm} - t_{PLHn}|,\ tos_{HL} = |\ t_{PHLm} - t_{PHLn}|$ 

## **Operating Characteristics**

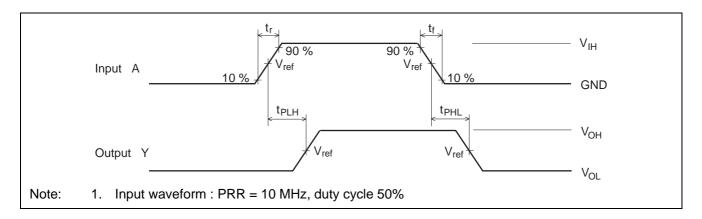
 $Ta=25^{\circ}C$ 

Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	Test conditions
Power dissipation	C <sub>PD</sub>	1.8	_	21	_	pF	f = 10 MHz
capacitance		2.5	_	22	_		
		3.3	_	23	_		
		5.0	_	27	_		

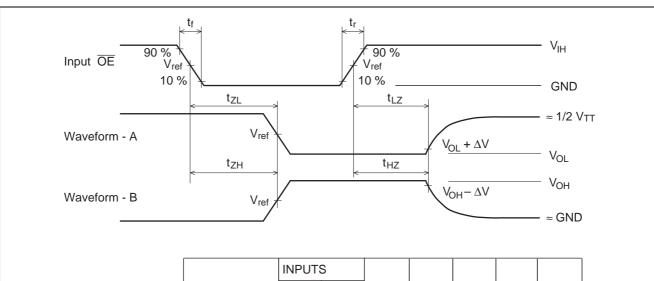
#### **Test Circuit**



#### Waveforms - 1



#### Waveforms - 2

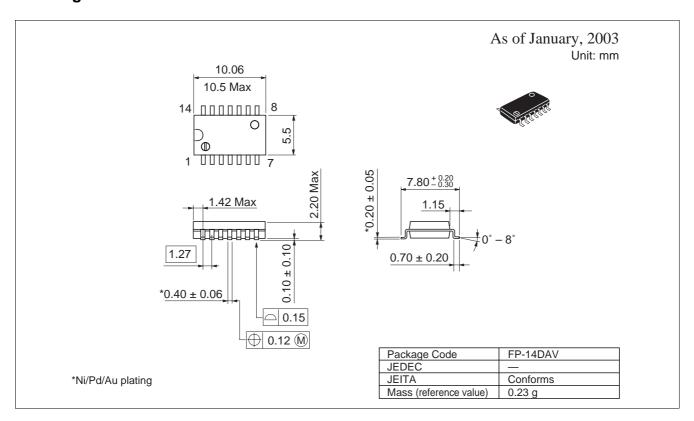


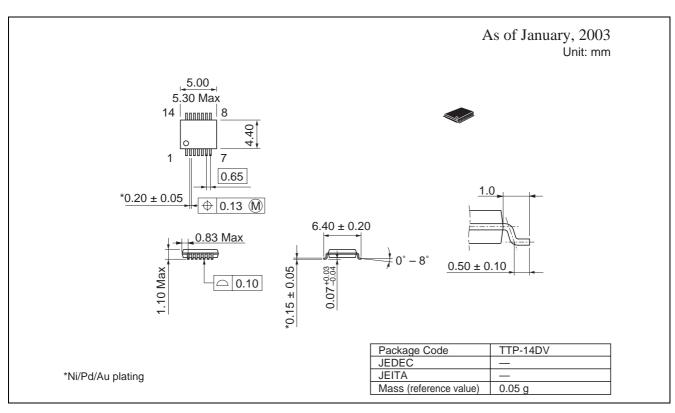
	INPUTS						
Vcc (V)	Vı	tr/tf	Vref	VTT	CL	RL	ΔV
Vcc = 1.8±0.15 V	Vcc	≤ 2 ns	1/2 Vcc	2× Vcc	30 pF	1.0 kΩ	0.15 V
Vcc = 2.5±0.2 V	Vcc	≤ 2 ns	1/2 Vcc	2× Vcc	30 pF	500 Ω	0.15 V
Vcc = 2.7 V	2.7 V	≤ 2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
Vcc = 3.3±0.3 V	2.7 V	≤ 2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
Vcc = 5.0±0.5 V	Vcc	≤ 2.5 ns	1/2 Vcc	2× Vcc	50 pF	500 Ω	0.3 V

Notes:

- 1. Input waveform : PRR = 10 MHz, duty cycle 50%
- 2. Waveform A shows input conditions such that the output is "L" level when enable by the output control.
- 3. Waveform B shows input conditions such that the output is "H" level when enable by the output control.

### **Package Dimensions**





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